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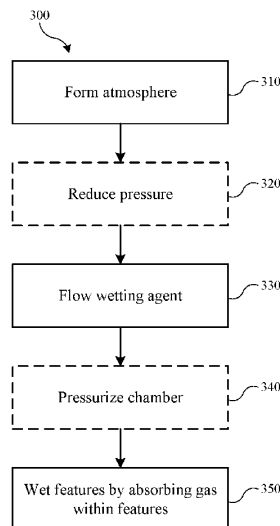


FIG. 3

(57) Abstract: Methods of wetting a semiconductor substrate may include forming a controlled atmosphere in a processing chamber housing the semiconductor substrate. The semiconductor substrate may define a plurality of features, which may include vias. The methods may include flowing a wetting agent into the processing chamber. A chamber pressure may be maintained below about 100 kPa. The methods may also include wetting the plurality of features defined in the substrate.

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